

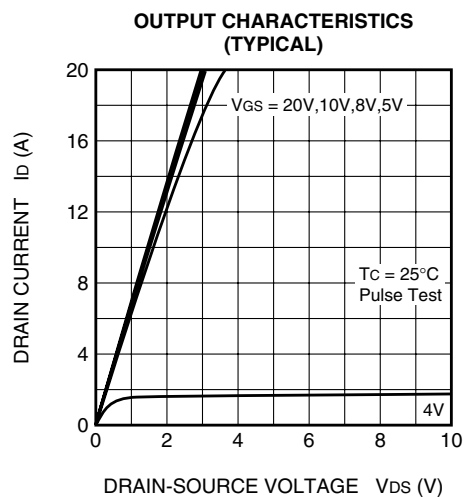
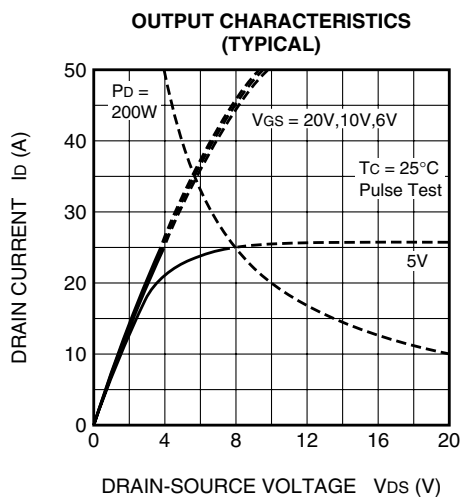
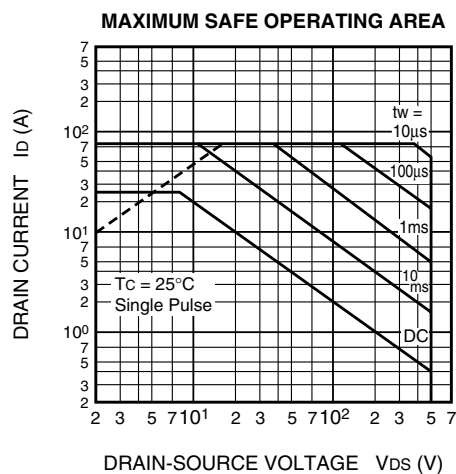
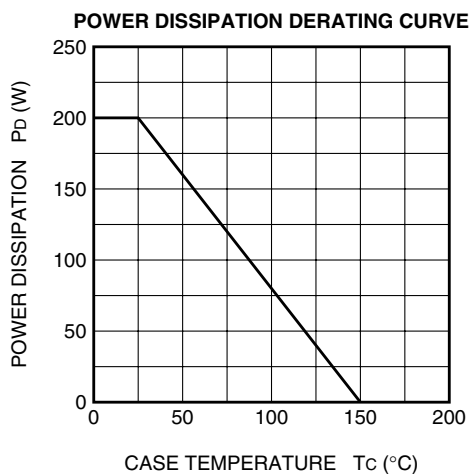
FS25SM-10A

HIGH-SPEED SWITCHING USE

ELECTRICAL CHARACTERISTICS (T_{ch} = 25°C)

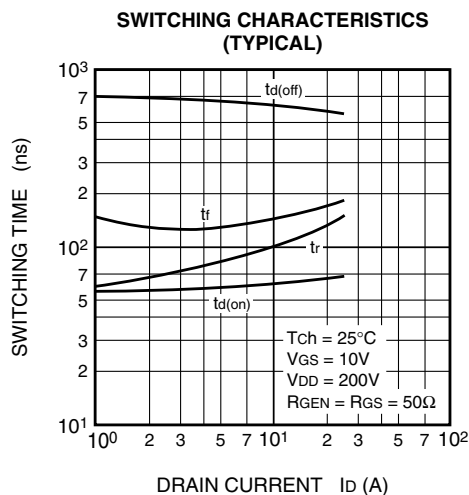
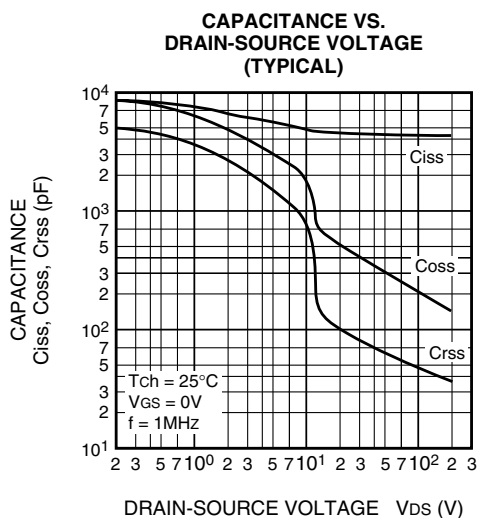
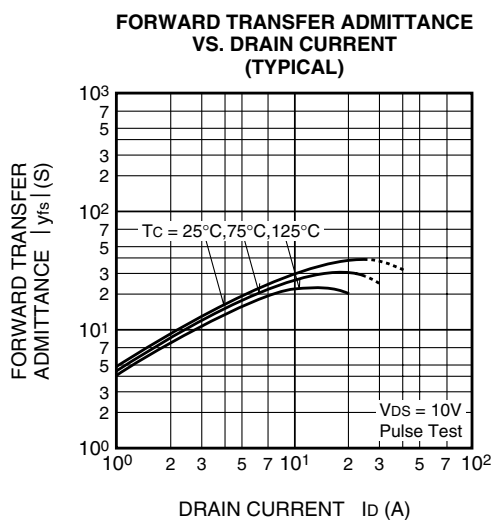
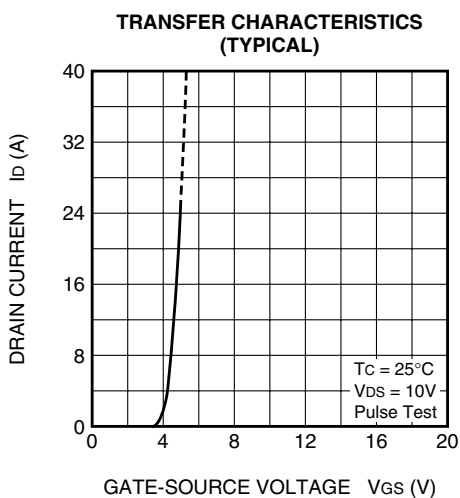
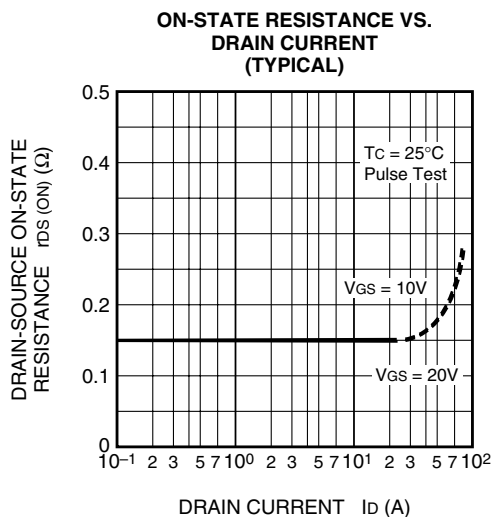
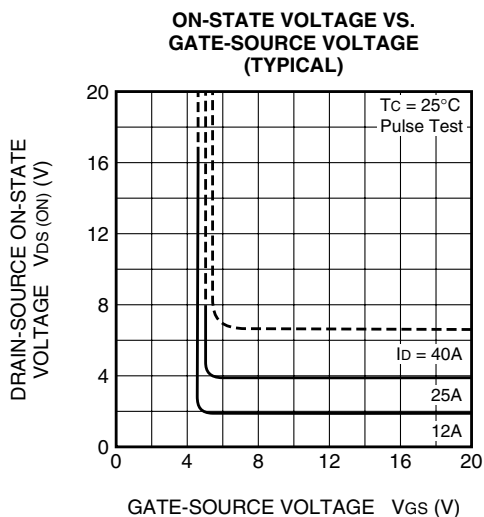
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
V (BR) DSS	Drain-source breakdown voltage	I _D = 1mA, V _{GS} = 0V	500	—	—	V
V (BR) GSS	Gate-source breakdown voltage	I _G = ±100μA, V _{DS} = 0V	±30	—	—	V
I _{GSS}	Gate-source leakage current	V _{GS} = ±25V, V _{DS} = 0V	—	—	±10	μA
I _{DSS}	Drain-source leakage current	V _{DS} = 500V, V _{GS} = 0V	—	—	1	mA
V _{GS} (th)	Gate-source threshold voltage	I _D = 1mA, V _{DS} = 10V	2.5	3.0	3.5	V
r _{DS} (ON)	Drain-source on-state resistance	I _D = 12A, V _{GS} = 10V	—	0.15	0.20	Ω
V _{DS} (ON)	Drain-source on-state voltage	I _D = 12A, V _{GS} = 10V	—	1.80	2.40	V
y _{fs}	Forward transfer admittance	I _D = 12A, V _{DS} = 10V	15.0	25.0	—	S
C _{iss}	Input capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz	—	4600	—	pF
C _{oss}	Output capacitance		—	460	—	pF
C _{rss}	Reverse transfer capacitance		—	100	—	pF
t _d (on)	Turn-on delay time	V _{DD} = 200V, I _D = 12A, V _{GS} = 10V, R _{GEN} = R _{GS} = 50Ω	—	60	—	ns
t _r	Rise time		—	100	—	ns
t _d (off)	Turn-off delay time		—	630	—	ns
t _f	Fall time		—	140	—	ns
V _{SD}	Source-drain voltage	I _S = 12A, V _{GS} = 0V	—	1.5	2.0	V
R _{th} (ch-c)	Thermal resistance	Channel to case	—	—	0.625	°C/W

PERFORMANCE CURVES



FS25SM-10A

HIGH-SPEED SWITCHING USE



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HIGH-SPEED SWITCHING USE

